IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Ge, *et al.*	Docket No.:	TSM03-0660
Serial No.:	10/699,574	Art Unit:	TBD
Filed:	October 31, 2003	Examiner:	TBD
For:	Strained Silicon Structure		

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Respectfully submitted,

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Filed:	October 31, 2003	Examiner:	TBD
Serial No.:	10/699,574	Art Unit:	2811
For:	STRAINED SILICON STRUCTURE		

Commissioner for Patents
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Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

Cite numbers 1-45 are newly cited prior art being filed under the waived requirement of 37 CFR 1.98 (a)(2)(i) dated July 11, 2003, therefore, copies of these U.S. patents are not included.

Respectfully submitted,

2/23/2004
Date

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 5

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Examiner Initials*	Cite No.[1]	Document Number Number - Kind Code[2] (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Sheet 2 of 5

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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Sheet 4 of 5

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